pixel electrode,

wherein an insulating layer is embedded in a recess portion provided at the contact portion,

wherein the insulating layer comprises a light absorbing layer comprising a resin in which a pigment or a carbon-based material is contained, and

E1 Cont'd

wherein an upper surface of said pixel electrode is substantially flush with said light absorbing insulating material.

2. (Amended) A display device comprising a pixel matrix circuit constituted by a plurality of pixels each including at least one TFT and a pixel electrode connected to the TFT,

wherein the pixel electrode includes a lamination structure of a first metal layer and a second metal layer;

wherein the first metal layer is in contact with the second metal layer,

an insulating layer is put between the first metal layer and the second metal layer at a contact portion where the first metal layer is connected with the TFT, and

wherein the insulating layer comprises a light absorbing layer comprising a resin in which a pigment or a carbon-based material is contained.

3. (Amended) A display device comprising a pixel matrix circuit comprising:

a TFT;

a first insulating layer over the TFT, wherein the first insulating layer comprises a contact hole;

a first conductive film over the first insulating film and in the contact hole, wherein the first conductive film is electrically connected to the TFT through the contact hole;

a second insulating layer filled in the contact hole, wherein an upper surface of the first conductive film outside the contact hole is not covered by the second insulating layer;

a second conductive film on and in contact with the upper surface of the first conductive film and the second insulating layer,

wherein the second insulating layer comprises a light absorbing layer comprising a resin in which a pigment or a carbon-based material is contained.

16. (Amended) An electronic device having at least one active matrix type liquid crystal panel, said liquid crystal panel comprising:

a substrate having an insulating surface;

an active matrix circuit formed over said substrate comprising a plurality of pixel electrodes, a plurality of switching elements for switching said pixel electrodes, respectively, an interlayer insulating film formed over said plurality of switching elements wherein each of said plurality of pixel electrodes is formed on said interlayer insulating film and electrically connected to the respective switching element through a contact hole of said interlayer insulating film; and

a driving circuit comprising a plurality of thin film transistors formed over said substrate for driving said active matrix circuit,

wherein a depression of said pixel electrode formed over said contact hole is filled with a light absorbing insulating material,

wherein the light absorbing insulating material comprises a resin in which a pigment or a carbon-based material is contained, and

wherein an upper surface of said pixel electrode is substantially flush with said light absorbing insulating material.

17. (Amended) An electronic device according to claim 16,

wherein each of said pixel electrodes comprises:

a first conductive layer which is formed on the interlayer insulating film and extends into said contact hole and electrically contacts the corresponding switching element; and

a second conductive layer which is formed on and in contact with the first conductive layer.

E2 cont'd

42. (Amended) An electronic device having at least one active matrix type display device comprising:

E3

at least one switching element;

at least one interlayer insulating film formed over said switching element;

a pixel electrode formed on said interlayer insulating film and electrically connected to said switching element through a contact hole of said interlayer insulating film;

a light absorbing insulating material formed in a depression of said pixel electrode over said contact hole,

wherein the light absorbing insulating material comprises a resin in which a pigment or a carbon-based material is contained, and

wherein an upper surface of said pixel electrode is substantially flush with said light absorbing insulating material.

48. (Amended) An electronic device having at least one active matrix type display device comprising:

E4

at least one switching element;

at least one interlayer insulating film formed over said switching element;

a pixel electrode formed on said interlayer insulating film and electrically connected to said switching element through a contact hole of said interlayer insulating film;

a light absorbing insulating material formed in a depression of said pixel electrode over said contact hole,

wherein said insulating material is a light absorbing material comprising a resin in which a pigment or a carbon-based material is contained, and

wherein an upper surface of said pixel electrode is substantially flush with said light absorbing insulating material.

81. (New) A display device according to claim 3, wherein the first conductive film is electrically connected to the TFT through one of a source electrode and a drain electrode thereof.